

NP16N06YLL

60 V – 16 A – N-channel Power MOS FET

Application: Automotive

R07DS1124EJ0100

Rev.1.00

Oct 30, 2013

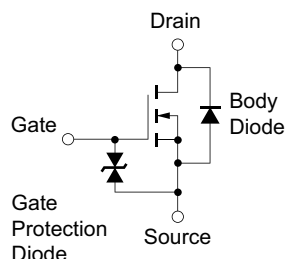
Description

These products are N-channel MOS Field Effect Transistors designed for high current switching applications.

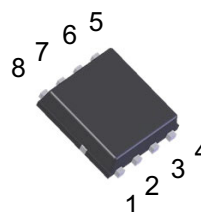
Features

- Low on-state resistance
— $R_{DS(on)} = 35 \text{ m}\Omega \text{ MAX.}$ ($V_{GS} = 10 \text{ V}$, $I_D = 8 \text{ A}$)
- Low C_{iss} : $C_{iss} = 400 \text{ pF TYP.}$ ($V_{DS} = 25 \text{ V}$, $V_{GS} = 0 \text{ V}$)
- Logic level drive type
- Gate to Source ESD protection diode built in
- Designed for automotive application and AEC-Q101 qualified

Outline



8-pin HSON



1, 2, 3 : Source
4 : Gate
5, 6, 7, 8: Drain

Remark: Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

Ordering Information

Part No.	Lead Plating	Packing		Package
NP16N06YLL-E1-AY ^{*1}	Pure Sn (Tin)	Tape 2500 p/reel	Taping (E1 type)	8-pin HSON
NP16N06YLL-E2-AY ^{*1}			Taping (E2 type)	

Note: ^{*1}. Pb-free (This product does not contain Pb in the external electrode)

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Drain to Source Voltage ($V_{GS} = 0\text{ V}$)	V_{DSS}	60	V
Gate to Source Voltage ($V_{DS} = 0\text{ V}$)	V_{GSS}	± 20	V
Drain Current (DC) ($T_C = 25^\circ\text{C}$)	$I_{D(DC)}$	± 16	A
Drain Current (pulse) ^{*1}	$I_{D(pulse)}$	± 32	A
Total Power Dissipation ($T_C = 25^\circ\text{C}$)	P_{T1}	27.3	W
Total Power Dissipation ($T_A = 25^\circ\text{C}$) ^{*2}	P_{T2}	1.25	W
Channel Temperature	T_{ch}	175	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +175	$^\circ\text{C}$
Single Avalanche Current ^{*3}	I_{AS}	10	A
Single Avalanche Energy ^{*3}	E_{AS}	10	mJ

Thermal Resistance

Channel to Case Thermal Resistance $R_{th(ch-C)}$ 5.49 $^\circ\text{C/W}$

Channel to Ambient Thermal Resistance ^{*2} $R_{th(ch-A)}$ 120.0 $^\circ\text{C/W}$

Notes: ^{*1}. $T_C = 25^\circ\text{C}$, $PW \leq 10\text{ }\mu\text{s}$, Duty Cycle $\leq 1\%$

^{*2}. Mounted on glass epoxy substrate of $40\text{ mm} \times 40\text{ mm} \times 1.6\text{ mm}$ with 4% copper area ($35\text{ }\mu\text{m}$)

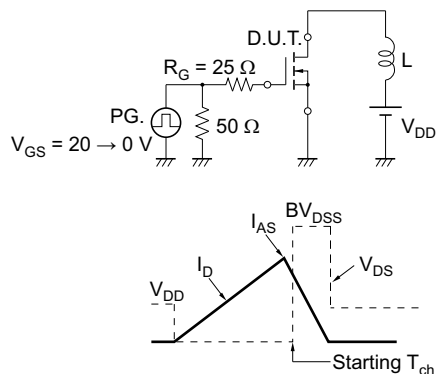
^{*3}. $T_{ch(start)} = 25^\circ\text{C}$, $V_{DD} = 30\text{ V}$, $R_G = 25\text{ }\Omega$, $L = 100\text{ }\mu\text{H}$, $V_{GS} = 20\text{ V} \rightarrow 0\text{ V}$

Electrical Characteristics (T_A = 25°C)

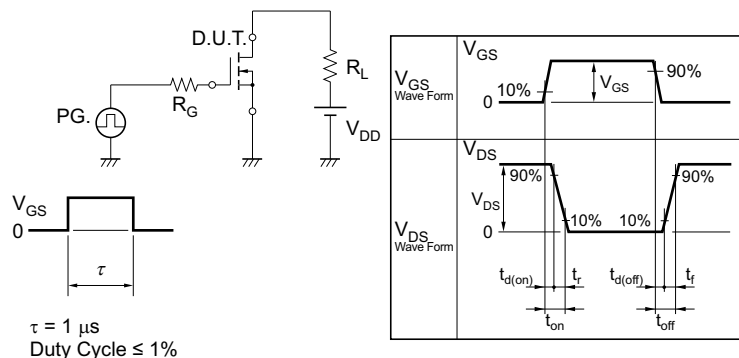
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	V _{DS} = 60 V, V _{GS} = 0 V
Gate Leakage Current	I _{GSS}			±10	μA	V _{GS} = ±20 V, V _{DS} = 0 V
Gate Cut-off Voltage	V _{GS(off)}	1.0	1.5	2.0	V	V _{DS} = 10 V, I _D = 1 mA
Forward Transfer Admittance *1	y _{fs}	5	12		S	V _{DS} = 5.0 V, I _D = 8 A
Drain to Source On-state Resistance *1	R _{DS(on)1}		31	35	mΩ	V _{GS} = 10 V, I _D = 8 A
	R _{DS(on)2}		42	55	mΩ	V _{GS} = 4.5 V, I _D = 8 A
Input Capacitance	C _{iss}		400	600	pF	V _{DS} = 25 V, V _{GS} = 0 V,
Output Capacitance	C _{oss}		84	130	pF	f = 1 MHz
Reverse Transfer Capacitance	C _{rss}		54	100	pF	
Turn-on Delay Time	t _{d(on)}		8	16	ns	V _{DD} = 30 V, I _D = 8 A, V _{GS} = 10 V, R _G = 0 Ω
Rise Time	t _r		8	20	ns	
Turn-off Delay Time	t _{d(off)}		25	50	ns	
Fall Time	t _f		5	12.5	ns	
Total Gate Charge	Q _G		12	18	nC	V _{DD} = 48 V, V _{GS} = 10 V, I _D = 16 A
Gate to Source Charge	Q _{GS}		1.4		nC	
Gate to Drain Charge	Q _{GD}		4		nC	
Body Diode Forward Voltage *1	V _{F(S-D)}		0.95	1.24	V	I _F = 16 A, V _{GS} = 0 V
Reverse Recovery Time	t _{rr}		27		ns	I _F = 16 A, V _{GS} = 0 V, di/dt = 100 A/μs
Reverse Recovery Charge	Q _{rr}		28		nC	

Note: *1. Pulsed test

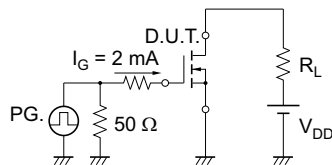
TEST CIRCUIT 1 AVALANCHE CAPABILITY



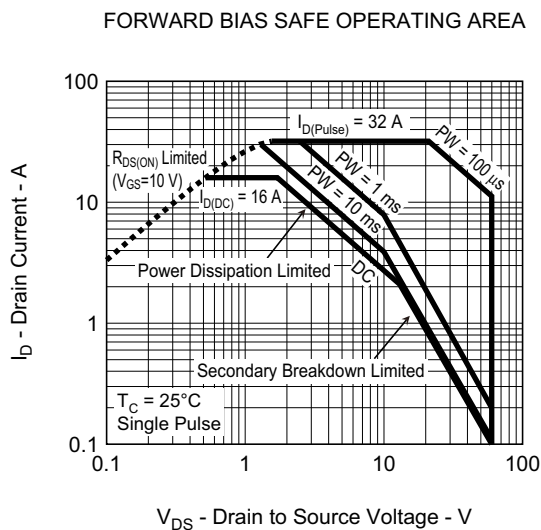
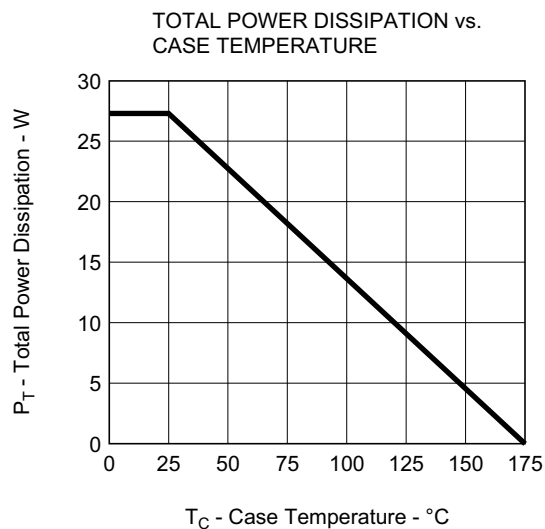
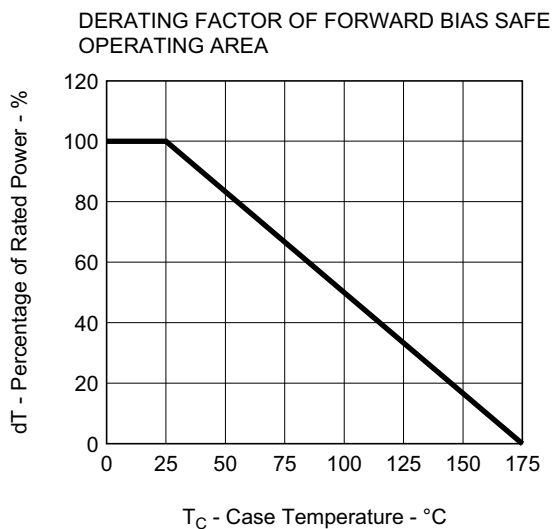
TEST CIRCUIT 2 SWITCHING TIME



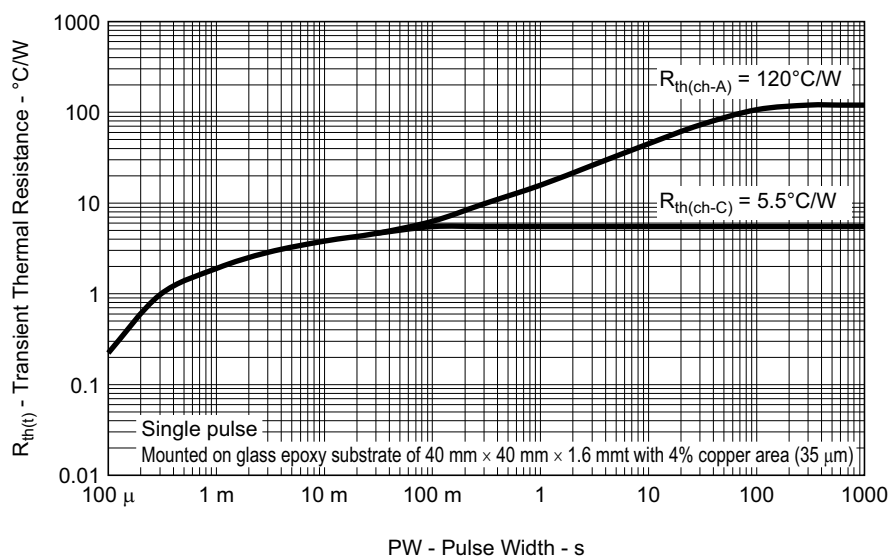
TEST CIRCUIT 3 GATE CHARGE

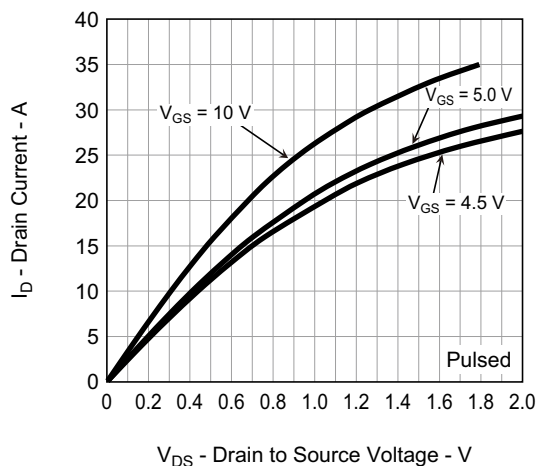


Typical Characteristics ($T_A = 25^\circ\text{C}$)

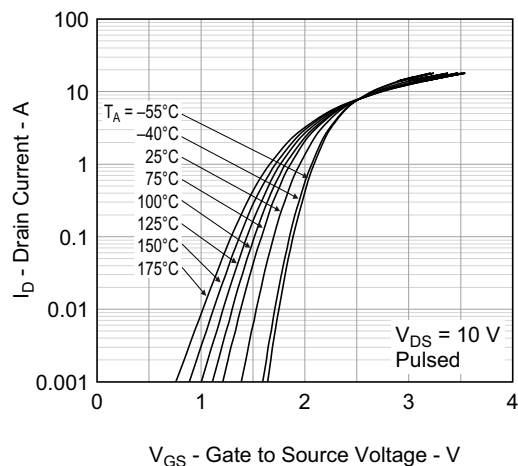
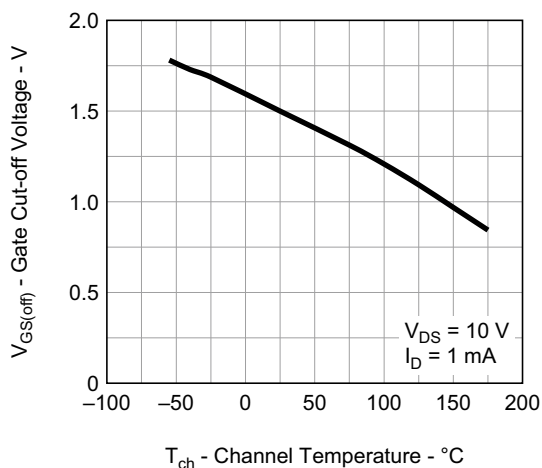
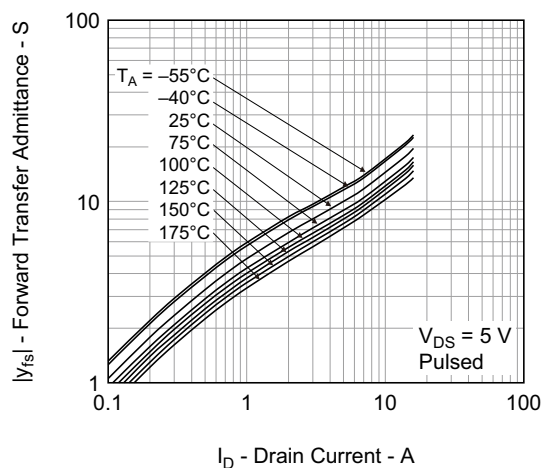
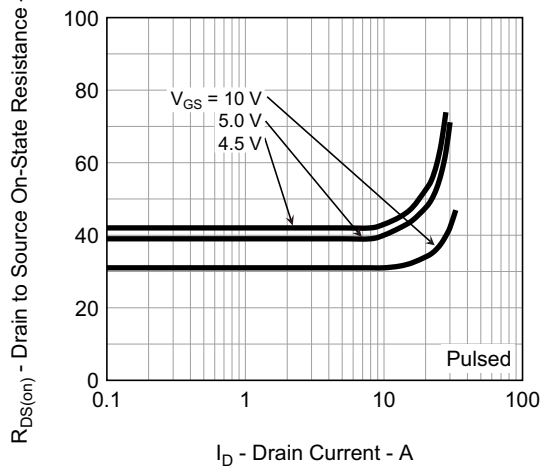
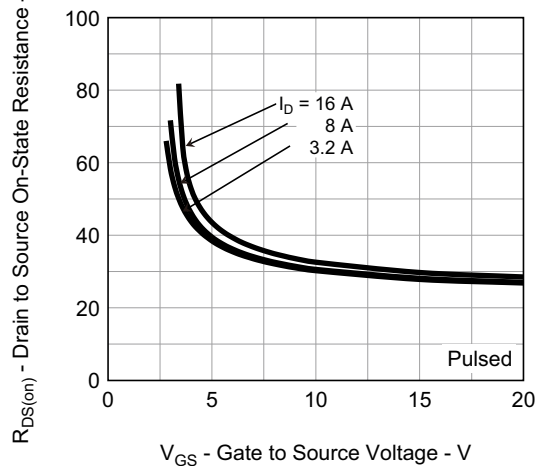


TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

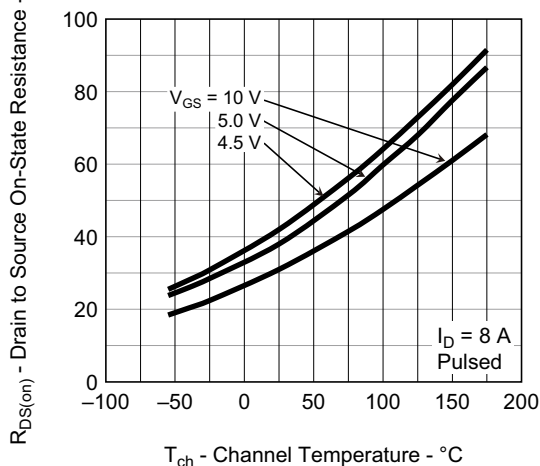


DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE

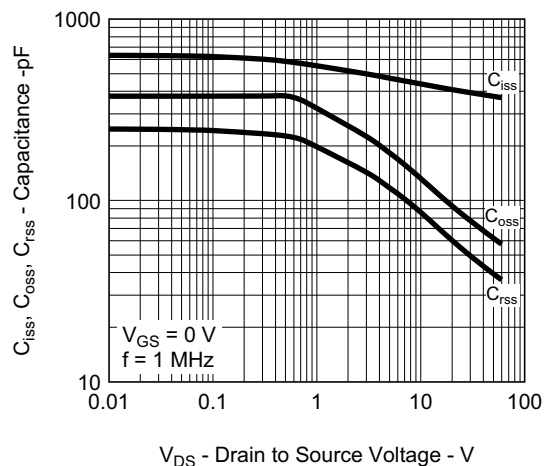
FORWARD TRANSFER CHARACTERISTICS

GATE CUT-OFF VOLTAGE vs.
CHANNEL TEMPERATUREFORWARD TRANSFER ADMITTANCE vs.
DRAIN CURRENTDRAIN TO SOURCE ON-STATE RESISTANCE vs.
DRAIN CURRENTDRAIN TO SOURCE ON-STATE RESISTANCE vs.
GATE TO SOURCE VOLTAGE

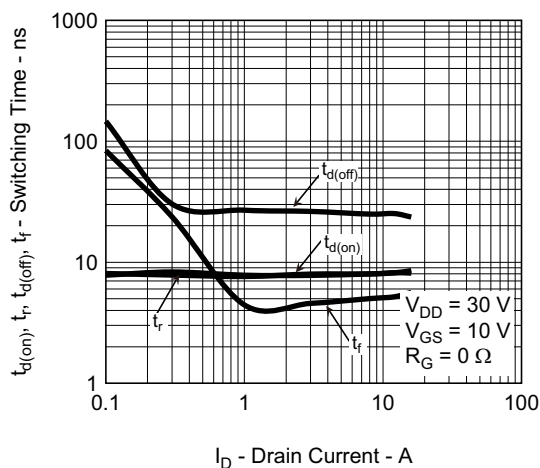
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



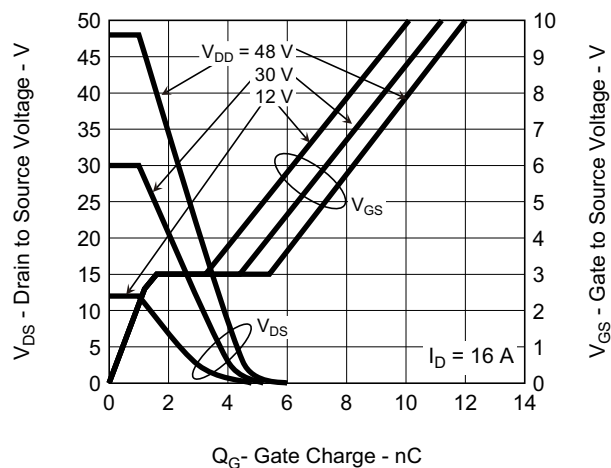
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



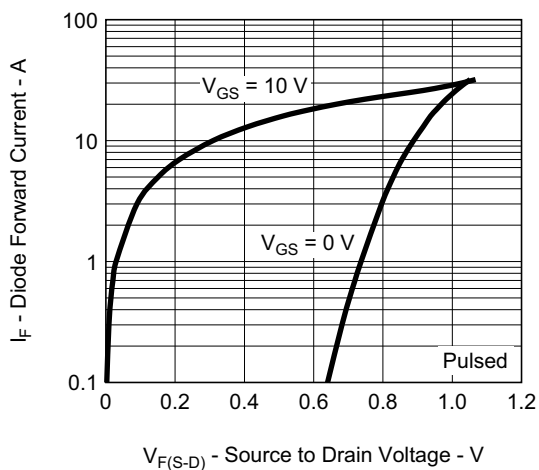
SWITCHING CHARACTERISTICS



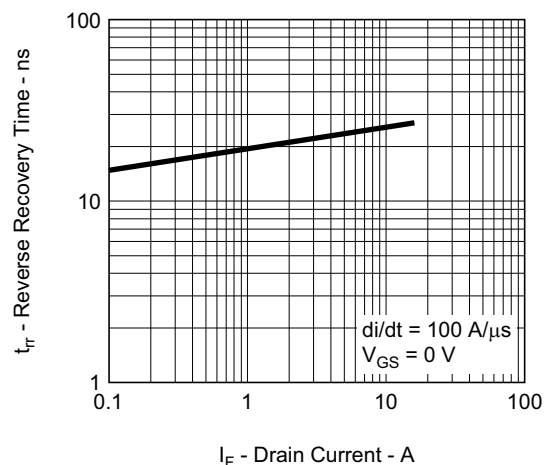
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE

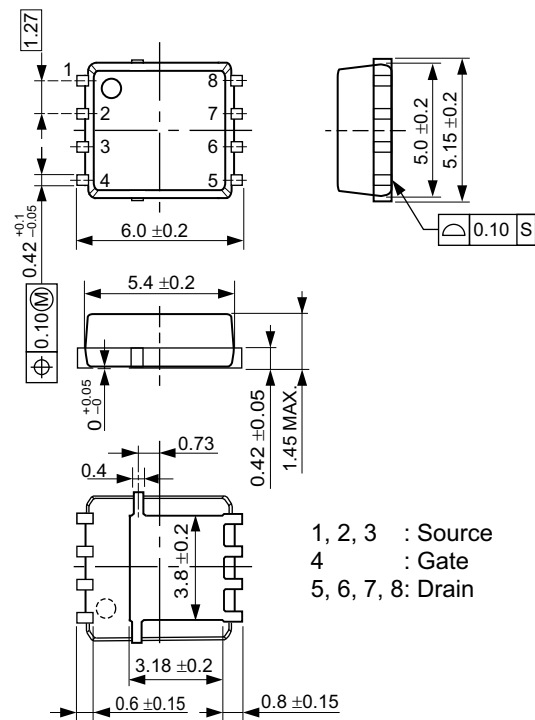


REVERSE RECOVERY TIME vs. DRAIN CURRENT



Package Drawings (Unit: mm)**8-pin HSON (Mass: 0.13 g TYP.)**

Renesas package code: PLSN0008KA-A



Revision History	NP16N06YLL Data Sheet
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Rev.	Date	Description	
		Page	Summary
1.00	Oct 30, 2013	—	First Edition Issued

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Renesas Electronics America Inc.

2880 Scott Boulevard Santa Clara, CA 95050-2554, U.S.A.
Tel: +1-408-588-6000, Fax: +1-408-588-6130

Renesas Electronics Canada Limited

1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada
Tel: +1-905-898-5441, Fax: +1-905-898-3220

Renesas Electronics Europe Limited

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: +44-1628-651-700, Fax: +44-1628-651-804

Renesas Electronics Europe GmbH

Arcadiastrasse 10, 40472 Düsseldorf, Germany
Tel: +49-211-65030, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.

7th Floor, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100083, P.R.China
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.

Unit 204, 205, AZIA Center, No.1233 Lujiazui Ring Rd., Pudong District, Shanghai 200120, China
Tel: +86-21-5877-1818, Fax: +86-21-6887-7858 / -7898

Renesas Electronics Hong Kong Limited

Unit 1601-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2886-9318, Fax: +852 2886-9022/9044

Renesas Electronics Taiwan Co., Ltd.

13F, No. 363, Fu Shing North Road, Taipei, Taiwan
Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

Renesas Electronics Singapore Pte. Ltd.

80 Bendemeer Road, Unit #06-02 Hyflux Innovation Centre Singapore 339949
Tel: +65-6213-0200, Fax: +65-6213-0300

Renesas Electronics Malaysia Sdn.Bhd.

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

Renesas Electronics Korea Co., Ltd.

11F., Samik Lavied' or Bldg., 720-2 Yeoksam-Dong, Kangnam-Ku, Seoul 135-080, Korea
Tel: +82-2-558-3737, Fax: +82-2-558-5141